BGU7008

SiGe:C Low Noise Amplifier MMIC for GPS, GLONASS and Galileo

Rev. 2 — 3 November 2011

Product data sheet

1. Product profile

1.1 General description

The BGU7008 is an AEC-Q100 qualified Low Noise Amplifier (LNA) for GNSS receiver applications in a plastic leadless 6-pin, extremely small SOT886 package. The BGU7008 requires only one external matching inductor and one external decoupling capacitor.

The BGU7008 adapts itself to the changing environment resulting from co-habitation of different radio systems in modern cellular handsets. It has been designed for low power consumption and optimal performance when jamming signals from co-existing cellular transmitters are present. At low jamming power levels it delivers 18.5 dB gain at a noise figure of 0.85 dB. During high jamming power levels, resulting for example from a cellular transmit burst, it temporarily increases its bias current to improve sensitivity.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- AEC-Q100 qualified (see Section 9.1)
- Covers full GNSS L1 band, from 1559 MHz to 1610 MHz
- Noise figure (NF) = 0.85 dB
- Gain 18.5 dB
- High input 1 dB compression point P_{i(1dB}) of -12 dBm
- High out of band IP3_i of 4 dBm
- Supply voltage 1.5 V to 2.85 V
- Power-down mode current consumption < 1 μA</p>
- Optimized performance at low supply current of 4.8 mA
- Integrated temperature stabilized bias for easy design
- Requires only one input matching inductor and one supply decoupling capacitor
- Input and output DC decoupled
- ESD protection on all pins (HBM > 2 kV)
- Integrated matching for the output
- Small 6-pin leadless package 1 mm × 1.45 mm × 0.5 mm
- 110 GHz transit frequency SiGe:C technology



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1.3 Applications

- LNA for GPS, GLONASS and Galileo in automotive applications like Toll Collection and Emergency Call.
- LNA for GPS in smart phones, feature phones, tablet PCs, Personal Navigation Devices, Digital Still Cameras, Digital Video Cameras, RF Front End modules, complete GPS chipset modules and theft protection (laptop, ATM).

1.4 Quick reference data

Table 1. Quick reference data

f = 1559 MHz to 1610 MHz; V_{CC} = 1.8 V; P_i < -40 dBm; T_{amb} = 25 °C; input matched to 50 Ω using a 5.6 nH inductor; unless otherwise specified.

	<u> </u>						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CC}	supply voltage	RF input AC coupled		1.5	-	2.85	V
I _{CC}	supply current	$V_{\text{ENABLE}} \geq 0.8 \ V$					
		$P_i < -40 \text{ dBm}$		3.4	4.8	6.1	mΑ
		$P_i = -20 \text{ dBm}$		8.9	12.8	15.9	mA
Gp	power gain	$P_i < -40$ dBm, no jammer		16.5	18.5	20.5	dB
		$P_i = -20$ dBm, no jammer		17.5	19.5	21.5	dB
NF	noise figure	$P_i < -40$ dBm, no jammer	<u>[1]</u>	-	0.85	1.2	dB
	F	P _i < −40 dBm, no jammer	[2]	-	0.90	1.3	dB
		$P_i = -20$ dBm, no jammer		-	1.2	1.6	dB
P _{i(1dB)}	input power at 1 dB	f = 1559 MHz to 1610 MHz					
	gain compression	V _{CC} = 1.5 V		-16	-13	-	dBm
		V _{CC} = 1.8 V		-15	-12	-	dBm
		$V_{CC} = 2.85 \text{ V}$		-14	-11	-	dBm
IP3 _i	input third-order intercept point	f = 1.575 GHz					
		V _{CC} = 1.5 V	[3]	1	4	-	dBm
		V _{CC} = 1.8 V	[3]	1	4	-	dBm
		V _{CC} = 2.85 V	[3]	2	5	_	dBm

^[1] PCB losses are subtracted.

2. Pinning information

Table 2. Pinning

Table 2.	Filling		
Pin	Description	Simplified outline	Graphic symbol
1	GND	6 5 4	
2	GND		4 5
3	RF_IN		3—6
4	V_{CC}		
5	ENABLE	1 2 3	2 1 sym129
6	RF_OUT	Transparent top view	•

^[2] Including PCB losses.

^[3] $f_1 = 1713 \text{ MHz}$; $f_2 = 1851 \text{ MHz}$; $P_1 = P_2 = -30 \text{ dBm}$.

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3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BGU7008	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886			

4. Marking

Table 4. Marking codes

Type number	Marking code
BGU7008	B7

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Min	Max	Unit
supply voltage	RF input AC coupled	-0.5	3.1	V
voltage on pin ENABLE	$V_{CC} \ge 2.5 \text{ V}$	-0.5	3.1	V
	V _{CC} < 2.5 V	[2] -0.5	$V_{CC} + 0.6$	V
voltage on pin RF_IN	DC			
	$V_{CC} \ge 3.0 \text{ V}$	[<u>3</u>] -0.5	3.6	V
	V _{CC} < 3.0 V	[2][3] -0.5	$V_{CC} + 0.6$	V
voltage on pin RF_OUT	DC			
	$V_{CC} \ge 1.8 \text{ V}$	[3] -0.5	3.6	V
	V _{CC} < 1.8 V	[2][3] -0.5	V _{CC} + 1.8	V
input power		-	0	dBm
total power dissipation	T _{sp} ≤ 130 °C	<u>[1]</u>	55	mW
storage temperature		-65	150	°C
junction temperature		-	150	°C
	supply voltage voltage on pin ENABLE voltage on pin RF_IN voltage on pin RF_OUT input power total power dissipation storage temperature	$\begin{array}{lll} \text{supply voltage} & \text{RF input AC coupled} \\ \text{voltage on pin ENABLE} & V_{\text{CC}} \geq 2.5 \text{ V} \\ \hline \text{Voltage on pin RF_IN} & DC \\ \hline & V_{\text{CC}} \geq 3.0 \text{ V} \\ \hline & V_{\text{CC}} < 3.0 \text{ V} \\ \hline \text{voltage on pin RF_OUT} & DC \\ \hline & V_{\text{CC}} < 3.0 \text{ V} \\ \hline & V_{\text{CC}} < 1.8 \text{ V} \\ \hline & V_{\text{CC}} < 1.8 \text{ V} \\ \hline \text{input power} \\ \hline \text{total power dissipation} & T_{\text{sp}} \leq 130 ^{\circ}\text{C} \\ \hline \text{storage temperature} \\ \hline \end{array}$	$\begin{array}{c} \text{supply voltage} & \text{RF input AC coupled} & -0.5 \\ \text{voltage on pin ENABLE} & V_{\text{CC}} \geq 2.5 \text{ V} & -0.5 \\ \hline V_{\text{CC}} < 2.5 \text{ V} & \boxed{21} -0.5 \\ \hline \text{voltage on pin RF_IN} & DC \\ \hline V_{\text{CC}} \geq 3.0 \text{ V} & \boxed{31} -0.5 \\ \hline V_{\text{CC}} < 3.0 \text{ V} & \boxed{213} -0.5 \\ \hline \text{voltage on pin RF_OUT} & DC \\ \hline \hline V_{\text{CC}} \geq 1.8 \text{ V} & \boxed{31} -0.5 \\ \hline V_{\text{CC}} < 1.8 \text{ V} & \boxed{31} -0.5 \\ \hline \text{input power} & - \\ \hline \text{total power dissipation} & T_{\text{sp}} \leq 130 ^{\circ}\text{C} & \boxed{11} \\ \hline \text{storage temperature} & -65 \\ \hline \end{array}$	$\begin{array}{llllllllllllllllllllllllllllllllllll$

^[1] T_{sp} is the temperature at the soldering point of the emitter lead.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		225	K/W

^[2] Due to internal ESD diode protection, the applied voltage should not exceed the specified maximum in order to avoid excess current.

^[3] The RF input and RF output are AC coupled through internal DC blocking capacitors.

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7. Characteristics

Table 7. Characteristics

f = 1559 MHz to 1610 MHz; V_{CC} = 1.8 V; V_{ENABLE} >= 0.8 V; P_i < -40 dBm; T_{amb} = 25 °C; input matched to 50 Ω using a 5.6 nH inductor; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage	RF input AC coupled	1.5	-	2.85	V
I _{CC}	supply current	$V_{\text{ENABLE}} \ge 0.8 \text{ V}$				
		$P_i < -40 \text{ dBm}$	3.4	4.8	6.1	mA
		$P_i = -20 \text{ dBm}$	8.9	12.8	15.9	mA
		$V_{\text{ENABLE}} \leq 0.35 \text{ V}$	-	-	1	μΑ
T_{amb}	ambient temperature		-40	+25	+125	°C
G_p	power gain	$T_{amb} = 25 ^{\circ}C$				
		$P_i < -40$ dBm, no jammer	16.5	18.5	20.5	dB
		$P_i = -20 \text{ dBm}$, no jammer	17.5	19.5	21.5	dB
		$P_{jam} = -20 \text{ dBm}; f_{jam} = 850 \text{ MHz}$	17.5	19.5	21.5	dB
		$P_{jam} = -20 \text{ dBm}; f_{jam} = 1850 \text{ MHz}$	17.5	19.5	21.5	dB
		$-40~^{\circ}\text{C} \le T_{amb} \le +125~^{\circ}\text{C}$				
		P _i < −40 dBm, no jammer	15.5	-	21	dB
		$P_i = -20$ dBm, no jammer	16.5	-	22	dB
		$P_{jam} = -20 \text{ dBm}$; $f_{jam} = 850 \text{ MHz}$	16.5	-	22	dB
		$P_{jam} = -20 \text{ dBm}; f_{jam} = 1850 \text{ MHz}$	16.5	-	22	dB
RL_{in}	input return loss	$P_i < -40 \text{ dBm}$	5	7	-	dB
		$P_i = -20 \text{ dBm}$	7	10	-	dB
RL_{out}	output return loss	$P_i < -40 \text{ dBm}$	12	18	-	dB
		$P_i = -20 \text{ dBm}$	15	24	-	dB
ISL	isolation		22	24	-	dB
NF	noise figure	T _{amb} = 25 °C				
		P _i < -40 dBm, no jammer [1]	-	0.85	1.2	dB
		P _i < -40 dBm, no jammer [2]	-	0.90	1.3	dB
		$P_i = -20$ dBm, no jammer	-	1.2	1.6	dB
		$P_{jam} = -20 \text{ dBm}; f_{jam} = 850 \text{ MHz}$	-	1.1	1.5	dB
		$P_{jam} = -20 \text{ dBm}; f_{jam} = 1850 \text{ MHz}$	-	1.3	1.7	dB
		$-40~^{\circ}\text{C} \le \text{T}_{amb} \le +125~^{\circ}\text{C}$				
		P _i < −40 dBm, no jammer	-	-	1.8	dB
		$P_i = -20$ dBm, no jammer	-	-	2.0	dB
		$P_{jam} = -20 \text{ dBm}; f_{jam} = 850 \text{ MHz}$	-	-	1.9	dB
		$P_{jam} = -20 \text{ dBm}; f_{jam} = 1850 \text{ MHz}$	-	-	2.1	dB

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Characteristics ... continued Table 7.

f = 1559 MHz to 1610 MHz; V_{CC} = 1.8 V; V_{ENABLE} >= 0.8 V; P_i < -40 dBm; T_{amb} = 25 °C; input matched to 50 Ω using a 5.6 nH inductor; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P _{i(1dB)}	input power at 1 dB gain compression	f = 1559 MHz to 1610 MHz				
		V _{CC} = 1.5 V	-16	-13	-	dBm
		V _{CC} = 1.8 V	-15	-12	-	dBm
		V _{CC} = 2.85 V	-14	-11	-	dBm
		f = 806 MHz to 928 MHz				
		V _{CC} = 1.5 V	<u>[3]</u> –16	-13	-	dBm
		V _{CC} = 1.8 V	<u>[3]</u> –15	-12	-	dBm
		V _{CC} = 2.85 V	<u>[3]</u> −15	-12	-	dBm
		f = 1612 MHz to 1909 MHz				
		V _{CC} = 1.5 V	<u>[3]</u> –14	-11	-	dBm
		V _{CC} = 1.8 V	[<u>3]</u> –13	-10	-	dBm
		V _{CC} = 2.85 V	<u>[3]</u> –11	-8	-	dBm
IP3 _i	input third-order intercept point	f = 1.575 GHz				
		V _{CC} = 1.5 V	<u>[4]</u> 1	4	-	dBm
		V _{CC} = 1.8 V	<u>[4]</u> 1	4	-	dBm
		V _{CC} = 2.85 V	<u>[4]</u> 2	5	-	dBm
t _{on}	turn-on time		<u>[5]</u> _	-	2	μS
t _{off}	turn-off time		<u>[5]</u> _	-	1	μS
K	Rollett stability factor		1	-	-	

^[1] PCB losses are subtracted.

Table 8. ENABLE (pin 5) $-40 \, ^{\circ}\text{C} \le T_{amb} \le +125 \, ^{\circ}\text{C}; \ 1.5 \, \text{V} \le V_{CC} \le 2.85 \, \text{V}$

V _{ENABLE} (V)	State
≤ 0.3	OFF
≥ 0.8	ON

^[2] Including PCB losses.

^[3] Out of band.

^[4] $f_1 = 1713 \text{ MHz}$; $f_2 = 1851 \text{ MHz}$; $P_1 = P_2 = -30 \text{ dBm}$.

^[5] Within 10 % of the final gain.

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8. Application information

8.1 GNSS LNA

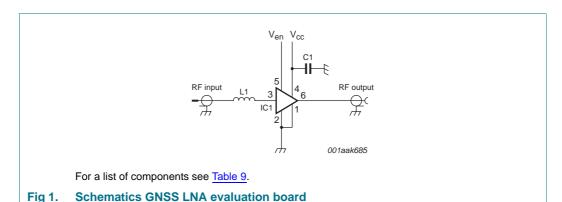
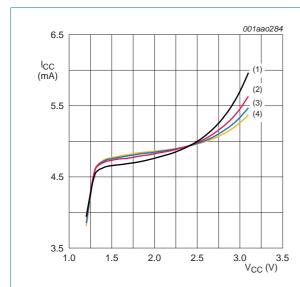


Table 9. List of components

For schematics see Figure 1.

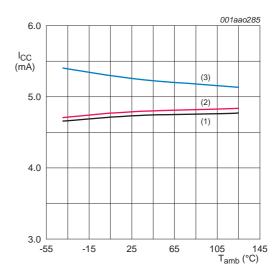
-				
Component	Description	Value	Supplier	Remarks
C1	decoupling capacitor	1 nF	various	
IC1	BGU7008	-	NXP	
L1	high quality matching inductor	5.6 nH	Murata LQW15A	



 $P_i = -45 \text{ dBm}.$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = +25 \, ^{\circ}C$
- (3) $T_{amb} = +85 \, ^{\circ}C$
- (4) $T_{amb} = +125 \, ^{\circ}C$

Fig 2. Supply current as a function of supply voltage; typical values

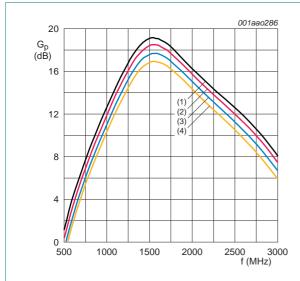


 $P_i = -45 \text{ dBm}.$

- (1) $V_{CC} = 1.5 \text{ V}$
- (2) $V_{CC} = 1.8 \text{ V}$
- (3) $V_{CC} = 2.85 \text{ V}$

Fig 3. Supply current as a function of ambient temperature; typical values

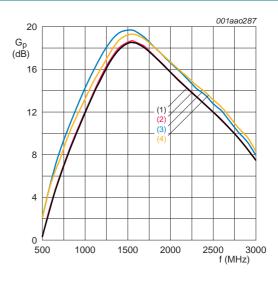
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 $V_{CC} = 1.8 \text{ V}; P_i = -45 \text{ dBm}.$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = +25 \, ^{\circ}C$
- (3) $T_{amb} = +85 \, ^{\circ}C$
- (4) $T_{amb} = +125 \, ^{\circ}C$

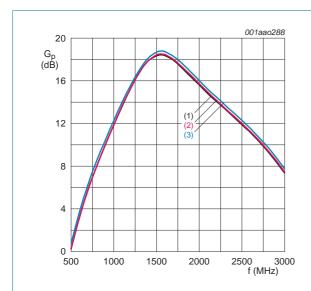
Fig 4. Power gain as a function of frequency; typical values



 V_{CC} = 1.8 V; T_{amb} = 25 °C.

- (1) $P_i = -45 \text{ dBm}$
- (2) $P_i = -30 \text{ dBm}$
- (3) $P_i = -20 \text{ dBm}$
- (4) $P_i = -15 \text{ dBm}$

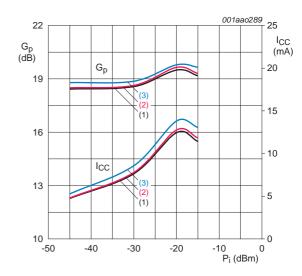
Fig 5. Power gain as a function of frequency; typical values



 $P_i = -45 \text{ dBm}$; $T_{amb} = 25 \,^{\circ}\text{C}$.

- (1) $V_{CC} = 1.5 \text{ V}$
- (2) $V_{CC} = 1.8 \text{ V}$
- (3) $V_{CC} = 2.85 \text{ V}$

Fig 6. Power gain as a function of frequency; typical values



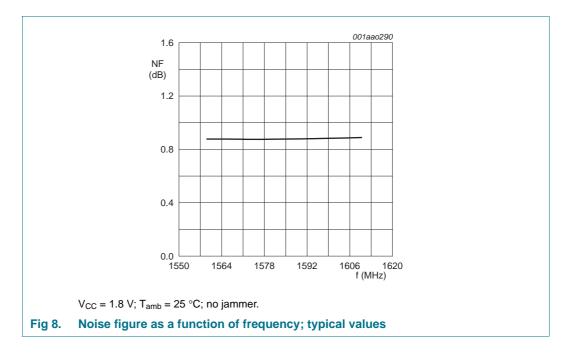
 $T_{amb} = 25 \, ^{\circ}C; f = 1575 \, MHz.$

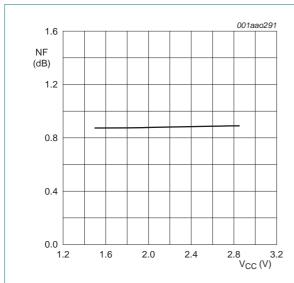
- (1) $V_{CC} = 1.5 \text{ V}$
- (2) $V_{CC} = 1.8 \text{ V}$
- (3) $V_{CC} = 2.85 \text{ V}$

Fig 7. Power gain as a function of input power; typical values

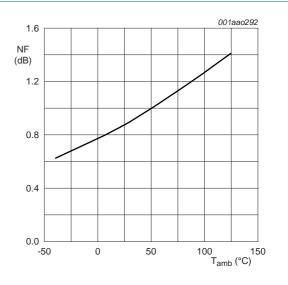
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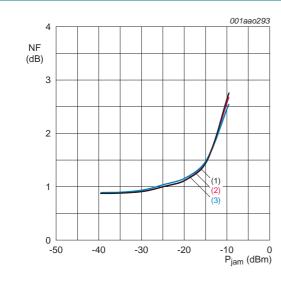
f = 1575 MHz; T_{amb} = 25 °C; no jammer. Noise figure as a function of supply voltage; Fig 9. typical values



f = 1575 MHz; $V_{CC} = 1.8 \text{ V}$; no jammer.

Fig 10. Noise figure as a function of ambient temperature; typical values

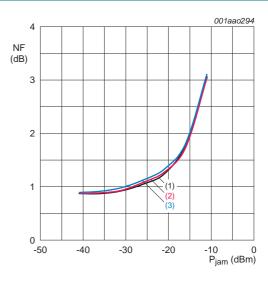
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 f_{jam} = 850 MHz; T_{amb} = 25 °C; f = 1575 MHz.

- (1) $V_{CC} = 1.5 \text{ V}$
- (2) $V_{CC} = 1.8 \text{ V}$
- (3) $V_{CC} = 2.85 \text{ V}$

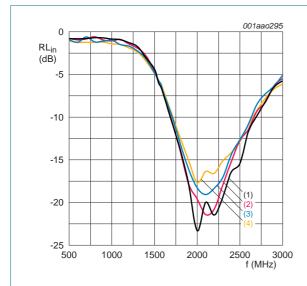
Fig 11. Noise figure as a function of jamming power; typical values



 f_{jam} = 1850 MHz; T_{amb} = 25 °C; f = 1575 MHz.

- (1) $V_{CC} = 1.5 \text{ V}$
- (2) $V_{CC} = 1.8 \text{ V}$
- (3) $V_{CC} = 2.85 \text{ V}$

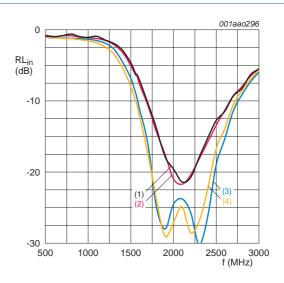
Fig 12. Noise figure as a function of jamming power; typical values



 $V_{CC} = 1.8 \text{ V}; P_i = -45 \text{ dBm}.$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = +25 \, ^{\circ}C$
- (3) $T_{amb} = +85 \, ^{\circ}C$
- (4) $T_{amb} = +125 \, ^{\circ}C$

Fig 13. Input return loss as a function of frequency; typical values

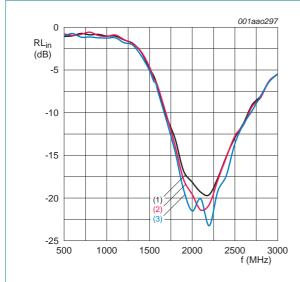


 V_{CC} = 1.8 V; T_{amb} = 25 °C.

- (1) $P_i = -45 \text{ dBm}$
- (2) $P_i = -30 \text{ dBm}$
- (3) $P_i = -20 \text{ dBm}$
- (4) $P_i = -15 \text{ dBm}$

Fig 14. Input return loss as a function of frequency; typical values

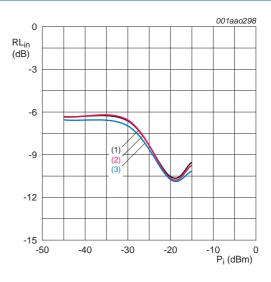
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 $P_i = -45 \text{ dBm}; T_{amb} = 25 \text{ }^{\circ}\text{C}.$

- (1) $V_{CC} = 1.5 \text{ V}$
- (2) $V_{CC} = 1.8 \text{ V}$
- (3) $V_{CC} = 2.85 \text{ V}$

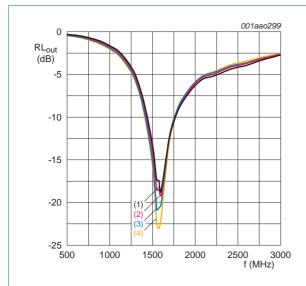
Fig 15. Input return loss as a function of frequency; typical values



 $T_{amb} = 25 \, ^{\circ}C; f = 1575 \, MHz.$

- (1) $V_{CC} = 1.5 \text{ V}$
- (2) $V_{CC} = 1.8 \text{ V}$
- (3) $V_{CC} = 2.85 \text{ V}$

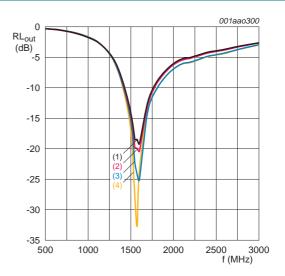
Fig 16. Input return loss as a function of input power; typical values



 $V_{CC} = 1.8 \text{ V}; P_i = -45 \text{ dBm}.$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = +25 \, ^{\circ}C$
- (3) $T_{amb} = +85 \, ^{\circ}C$
- (4) $T_{amb} = +125 \, ^{\circ}C$

Fig 17. Output return loss as a function of frequency; typical values

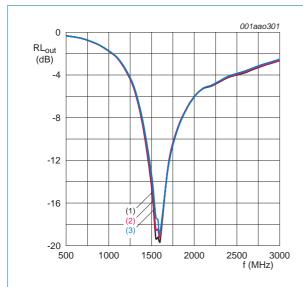


 $V_{CC} = 1.8 \text{ V}; T_{amb} = 25 \,^{\circ}\text{C}.$

- (1) $P_i = -45 \text{ dBm}$
- (2) $P_i = -30 \text{ dBm}$
- (3) $P_i = -20 \text{ dBm}$
- (4) $P_i = -15 \text{ dBm}$

Fig 18. Output return loss as a function of frequency; typical values

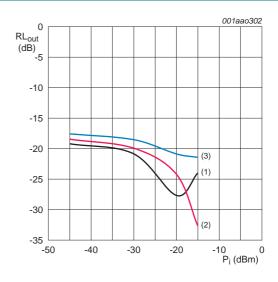
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 $P_i = -45 \text{ dBm}; T_{amb} = 25 \text{ }^{\circ}\text{C}.$

- (1) $V_{CC} = 1.5 \text{ V}$
- (2) $V_{CC} = 1.8 \text{ V}$
- (3) $V_{CC} = 2.85 \text{ V}$

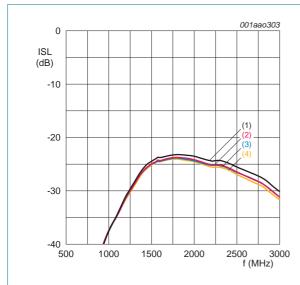
Fig 19. Output return loss as a function of frequency; typical values



 $T_{amb} = 25 \, ^{\circ}C; f = 1575 \, MHz.$

- (1) $V_{CC} = 1.5 \text{ V}$
- (2) $V_{CC} = 1.8 \text{ V}$
- (3) $V_{CC} = 2.85 \text{ V}$

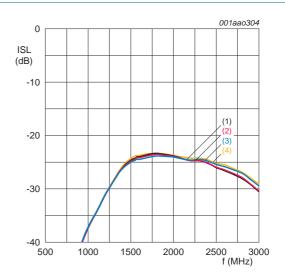
Fig 20. Output return loss as a function of input power; typical values



 $V_{CC} = 1.8 \text{ V}; P_i = -45 \text{ dBm}.$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = +25 \, ^{\circ}C$
- (3) $T_{amb} = +85 \, ^{\circ}C$
- (4) $T_{amb} = +125 \, ^{\circ}C$

Fig 21. Isolation as a function of frequency; typical values

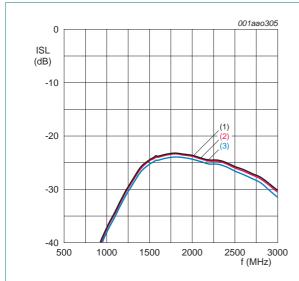


 $V_{CC} = 1.8 \text{ V}; T_{amb} = 25 \,^{\circ}\text{C}.$

- (1) $P_i = -45 \text{ dBm}$
- (2) $P_i = -30 \text{ dBm}$
- (3) $P_i = -20 \text{ dBm}$
- (4) $P_i = -15 \text{ dBm}$

Fig 22. Isolation as a function of frequency; typical values

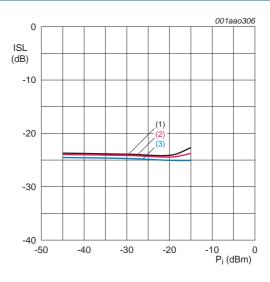
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 $P_i = -45 \text{ dBm}; T_{amb} = 25 \text{ }^{\circ}\text{C}.$

- (1) $V_{CC} = 1.5 \text{ V}$
- (2) $V_{CC} = 1.8 \text{ V}$
- (3) $V_{CC} = 2.85 \text{ V}$

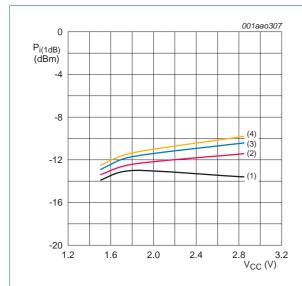
Fig 23. Isolation as a function of frequency; typical values



 $T_{amb} = 25 \, ^{\circ}C; f = 1575 \, MHz.$

- (1) $V_{CC} = 1.5 \text{ V}$
- (2) $V_{CC} = 1.8 \text{ V}$
- (3) $V_{CC} = 2.85 \text{ V}$

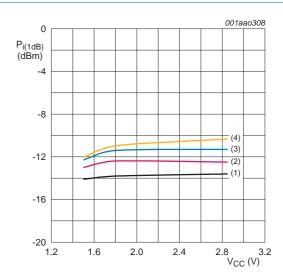
Fig 24. Isolation as a function of input power; typical values



f = 1575 MHz.

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = +25 \, ^{\circ}C$
- (3) $T_{amb} = +85 \, ^{\circ}C$
- (4) $T_{amb} = +125 \, ^{\circ}C$

Fig 25. Input power at 1 dB gain compression as a function of supply voltage; typical values



f = 850 MHz.

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = +25 \, ^{\circ}C$
- (3) $T_{amb} = +85 \, ^{\circ}C$
- (4) $T_{amb} = +125 \, ^{\circ}C$

Fig 26. Input power at 1 dB gain compression as a function of supply voltage; typical values

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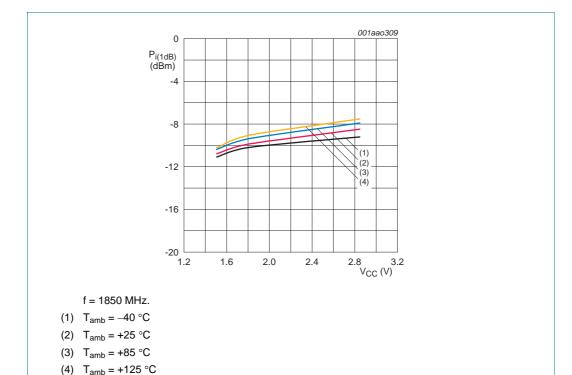
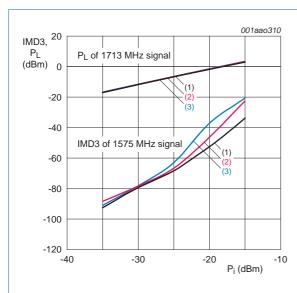


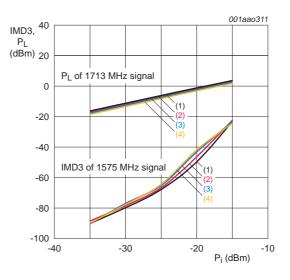
Fig 27. Input power at 1 dB gain compression as a function of supply voltage



f = 1575 MHz; $f_1 = 1713 \text{ MHz}$; $f_2 = 1851 \text{ MHz}$; $T_{amb} = 25 \,^{\circ}\text{C}$.

- (1) $V_{CC} = 1.5 \text{ V}$
- (2) $V_{CC} = 1.8 \text{ V}$
- (3) $V_{CC} = 2.85 \text{ V}$

Fig 28. Third order intermodulation distortion and output power as function of input power; typical values

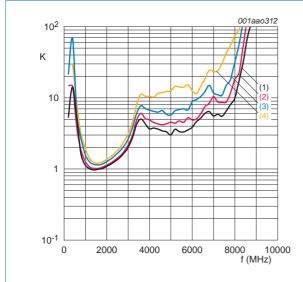


 $f = 1575 \text{ MHz}; f_1 = 1713 \text{ MHz}; f_2 = 1851 \text{ MHz}; V_{CC} = 1.8 \text{ V}.$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = +25 \, ^{\circ}C$
- (3) $T_{amb} = +85 \, ^{\circ}C$
- (4) $T_{amb} = +125 \, ^{\circ}C$

Fig 29. Third order intermodulation distortion and output power as function of input power; typical values

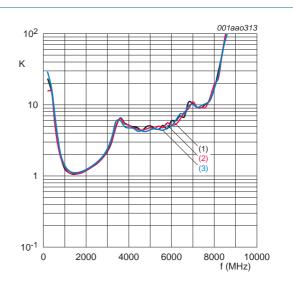
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 $V_{CC} = 1.8 \text{ V}; P_i = -45 \text{ dBm}.$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = +25 \, ^{\circ}C$
- (3) $T_{amb} = +85 \, ^{\circ}C$
- (4) $T_{amb} = +125 \, ^{\circ}C$

Fig 30. Rollett stability factor as a function of frequency; typical values



 $T_{amb} = 25 \, ^{\circ}C; \, P_i = -45 \, dBm.$

- (1) $V_{CC} = 1.5 \text{ V}$
- (2) $V_{CC} = 1.8 \text{ V}$
- (3) $V_{CC} = 2.85 \text{ V}$

Fig 31. Rollett stability factor as a function of frequency; typical values

9. Test information

9.1 Quality information

All qualification tests are performed according AEC-Q100 except for read point testing (final test of qualification sample). Which is done only at room temperature.

As part of the zero defect program, the following is part of the industrial test flow:

- Part Average Testing
- Maverick Lot Handling at assembly factory

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10. Package outline

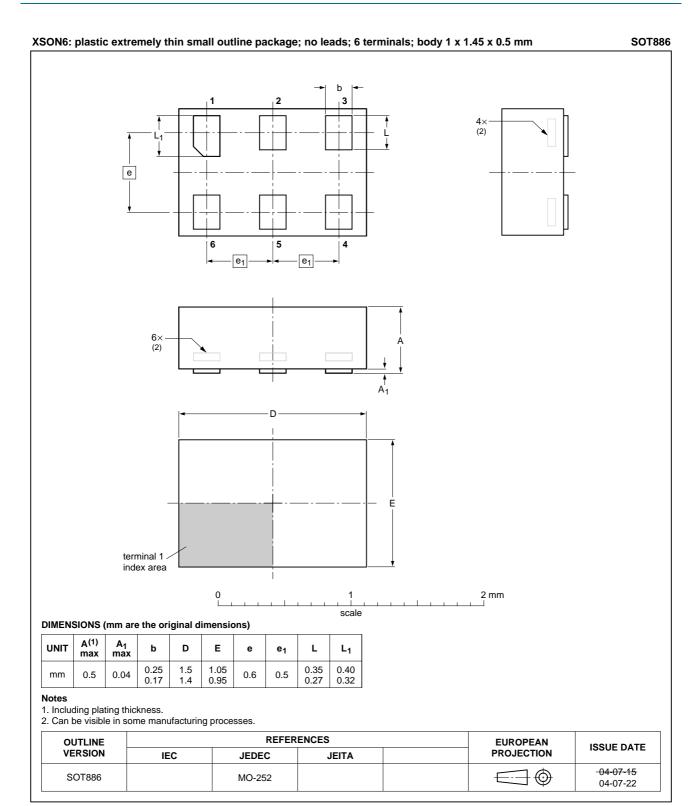


Fig 32. Package outline SOT886 (XSON6)

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11. Abbreviations

Table 10. Abbreviations

AC A	Description Alternating Current Automotive Electronics Council
AEC A	Automotive Electronics Council
ATM A	Automated Teller Machine (cash dispenser)
DC D	Direct Current
GLONASS G	GLObal NAvigation Satellite System
GNSS G	Global Navigation Satellite System
GPS G	Global Positioning System
HBM F	Human Body Model
MMIC N	Monolithic Microwave Integrated Circuit
PC F	Personal Computer
PCB F	Printed Circuit Board
RF R	Radio Frequency
SiGe:C	Silicon Germanium Carbon

12. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BGU7008 v.2	20111103	Product data sheet	-	BGU7008 v.1	
Modifications: • Figure 25: f = 850 MHz changed to f = 1575 MHz • Figure 26: f = 1850 MHz changed to f = 850 MHz • Figure 27: f = 1575 MHz changed to f = 1850 MHz					
BGU7008 v.1	20110822	Product data sheet	-	-	

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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